

Automotive-grade N-Channel 40 V, 5.5 mΩ typ., 80 A STripFET™ F6 Power MOSFET in a D²PAK package

Datasheet - production data

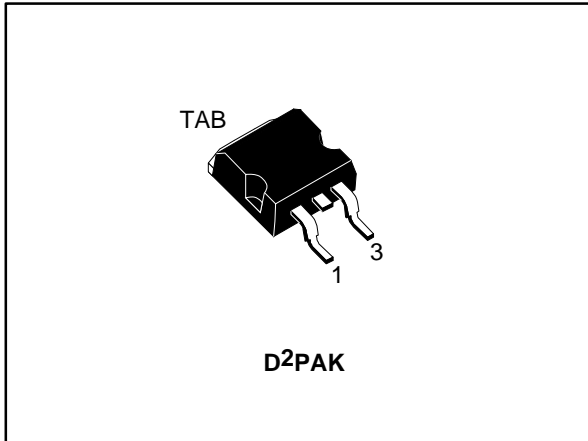
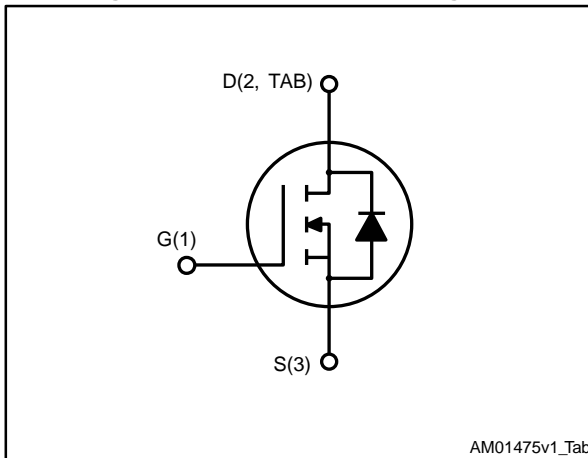


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STB80N4F6AG	40 V	6 mΩ	80 A

- Designed for automotive applications and AEC-Q101 qualified
- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the STripFET™ F6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R_{DS(on)} in all packages.

Table 1: Device summary

Order code	Marking	Package	Packaging
STB80N4F6AG	80N4F6	D ² PAK	Tape and Reel

Contents

- 1 Electrical ratings 3**
- 2 Electrical characteristics 4**
 - 2.1 Electrical characteristics (curves) 6
- 3 Test circuits 8**
- 4 Package mechanical data 9**
 - 4.1 D²PAK package information 9
 - 4.2 D²PAK packing information 12
- 5 Revision history 14**



1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage	40	V
V _{GS}	Gate-source voltage	± 20	V
I _D	Drain current (continuous) at T _C = 25 °C	80	A
I _D	Drain current (continuous) at T _C = 100 °C	56	A
I _{DM} ⁽¹⁾	Drain current (pulsed)	320	A
P _{TOT}	Total dissipation at T _C = 25 °C	70	W
I _{AV}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _J max)	40	A
E _{AS}	Single pulse avalanche energy(Starting T _J = 25 °C, = I _D =I _{AV} , V _{DD} = 25 V)	149	mJ
T _{stg}	Storage temperature	- 55 to 175	°C
T _j	Max. operating junction temperature	175	°C

Notes:

⁽¹⁾ Pulse width limited by safe operating area.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max.	2.14	°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-ambient max.	35	°C/W

Notes:

⁽¹⁾When mounted on FR-4 board of inch2, 2 oz Cu

2 Electrical characteristics

($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified).

Table 4: On/Off States

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	40			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0\text{ V}$)	$V_{DS} = 40\text{ V}$			1	μA
		$V_{DS} = 40\text{ V}$ $T_j = 125\text{ }^\circ\text{C}$			100	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0\text{ V}$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$		5.5	6	m Ω

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	2150	-	pF
C_{oss}	Output capacitance		-	335	-	pF
C_{rss}	Reverse transfer capacitance		-	160	-	pF
Q_g	Total gate charge	$V_{DD} = 20\text{ V}$, $I_D = 80\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 14: "Test circuit for gate charge behavior")	-	36	-	nC
Q_{gs}	Gate-source charge		-	11	-	nC
Q_{gd}	Gate-drain charge		-	9	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15: "Test circuit for inductive load switching and diode recovery times")	-	10.5	-	ns
t_r	Rise time		-	7.6	-	ns
$t_{d(off)}$	Turn-off-delay time		-	46.1	-	ns
t_f	Fall time		-	11.9	-	ns

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source drain current				80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}= 40\text{ A}$, $V_{GS}= 0\text{ V}$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD}= 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD}= 32\text{ V}$ (See Figure 17: "Unclamped inductive waveform")		41.1		ns
Q_{RR}	Reverse recovery charge			43.6		nC
I_{RRM}	Reverse recovery current			2.1		A

Notes:

(1)Pulse width limited by safe operating area.

(2)Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

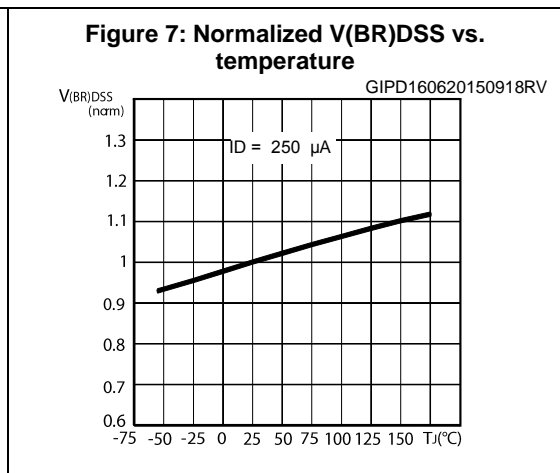
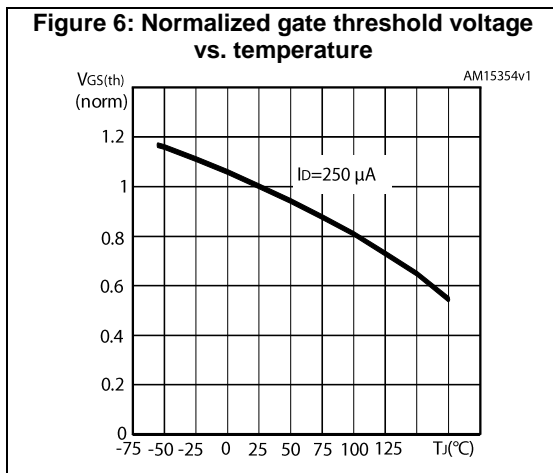
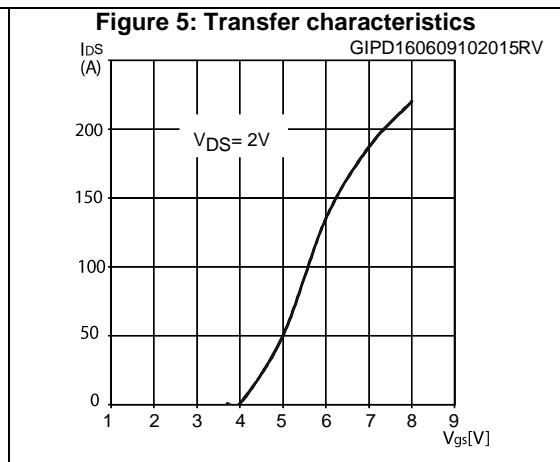
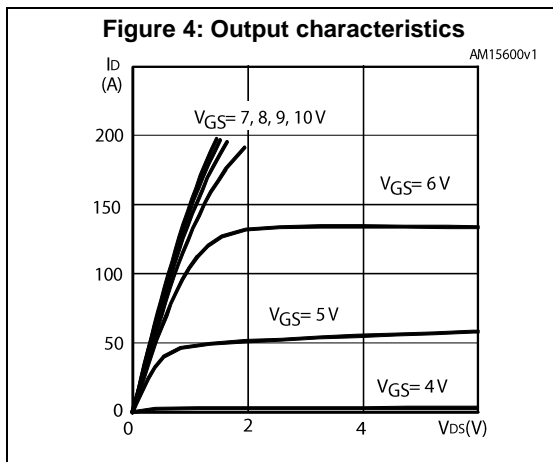
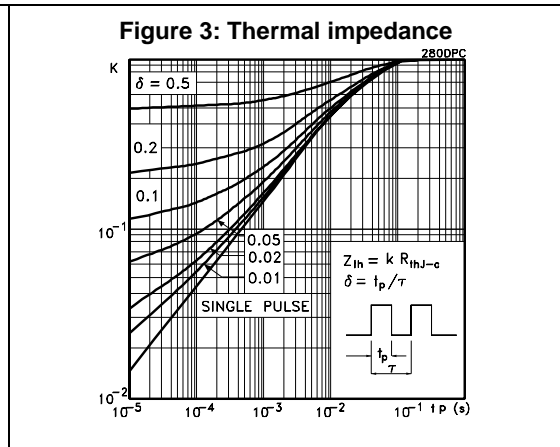
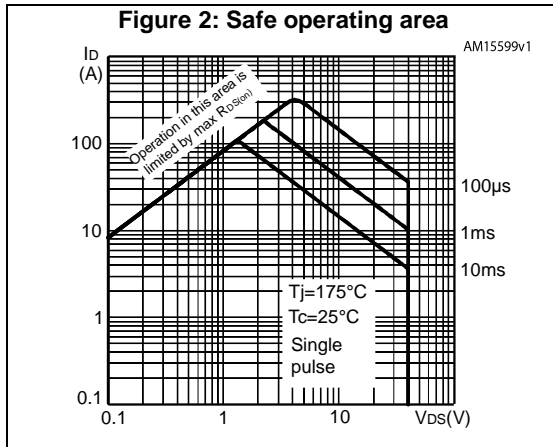


Figure 8: Static drain-source on-resistance

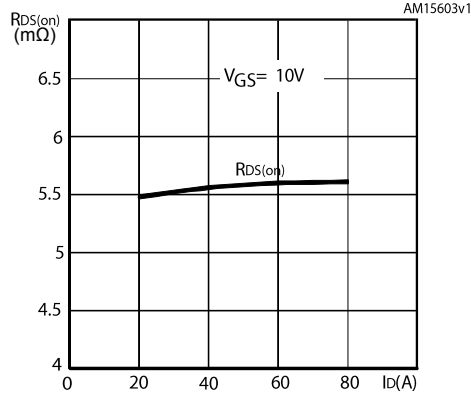


Figure 9: Normalized on-resistance vs. temperature

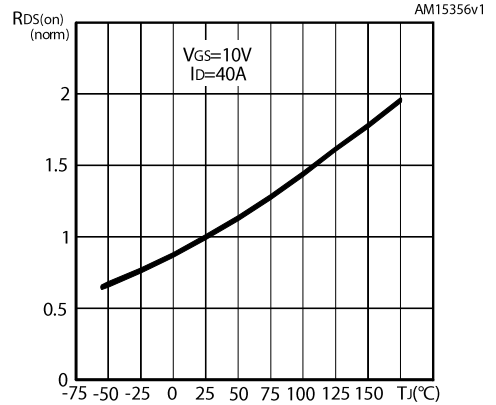


Figure 10: Gate charge vs. gate-source voltage

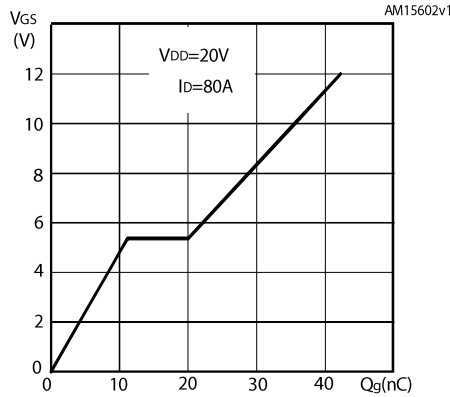


Figure 11: Capacitance variations

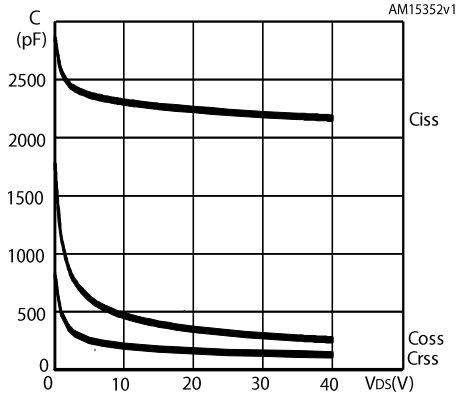
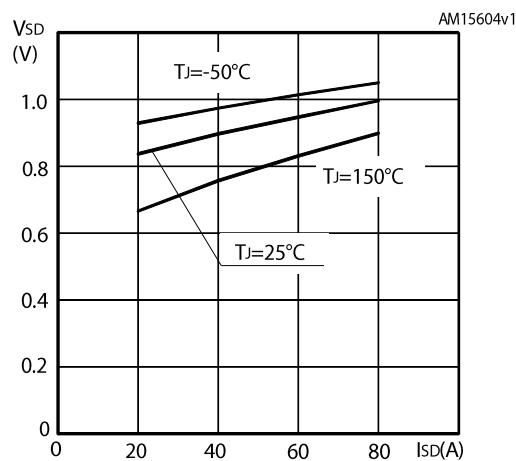
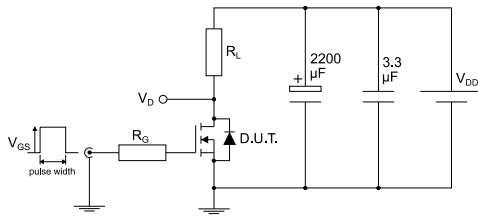


Figure 12: Source- drain diode forward characteristics



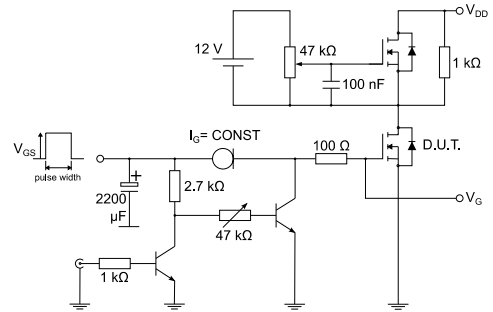
3 Test circuits

Figure 13: Test circuit for resistive load switching times



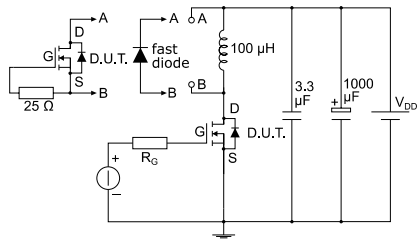
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Figure 14: Test circuit for gate charge behavior



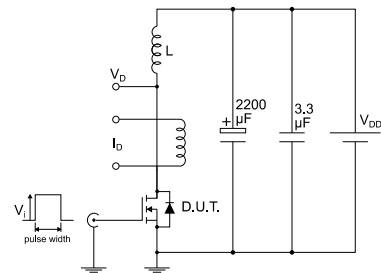
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Figure 15: Test circuit for inductive load switching and diode recovery times



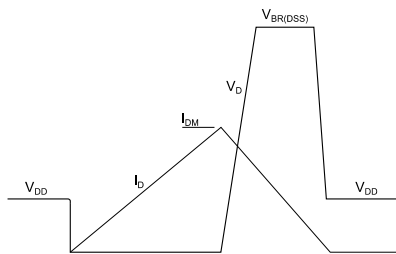
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Figure 16: Unclamped inductive load test circuit



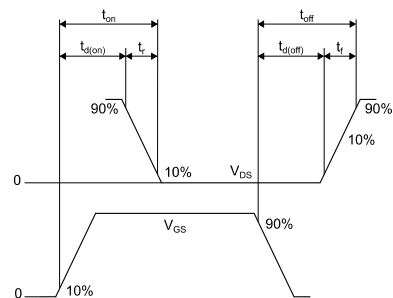
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Figure 17: Unclamped inductive waveform



AM01472v1

Figure 18: Switching time waveform



AM01473v1

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 D²PAK package information

Figure 19: D²PAK (TO-263) type A package outline

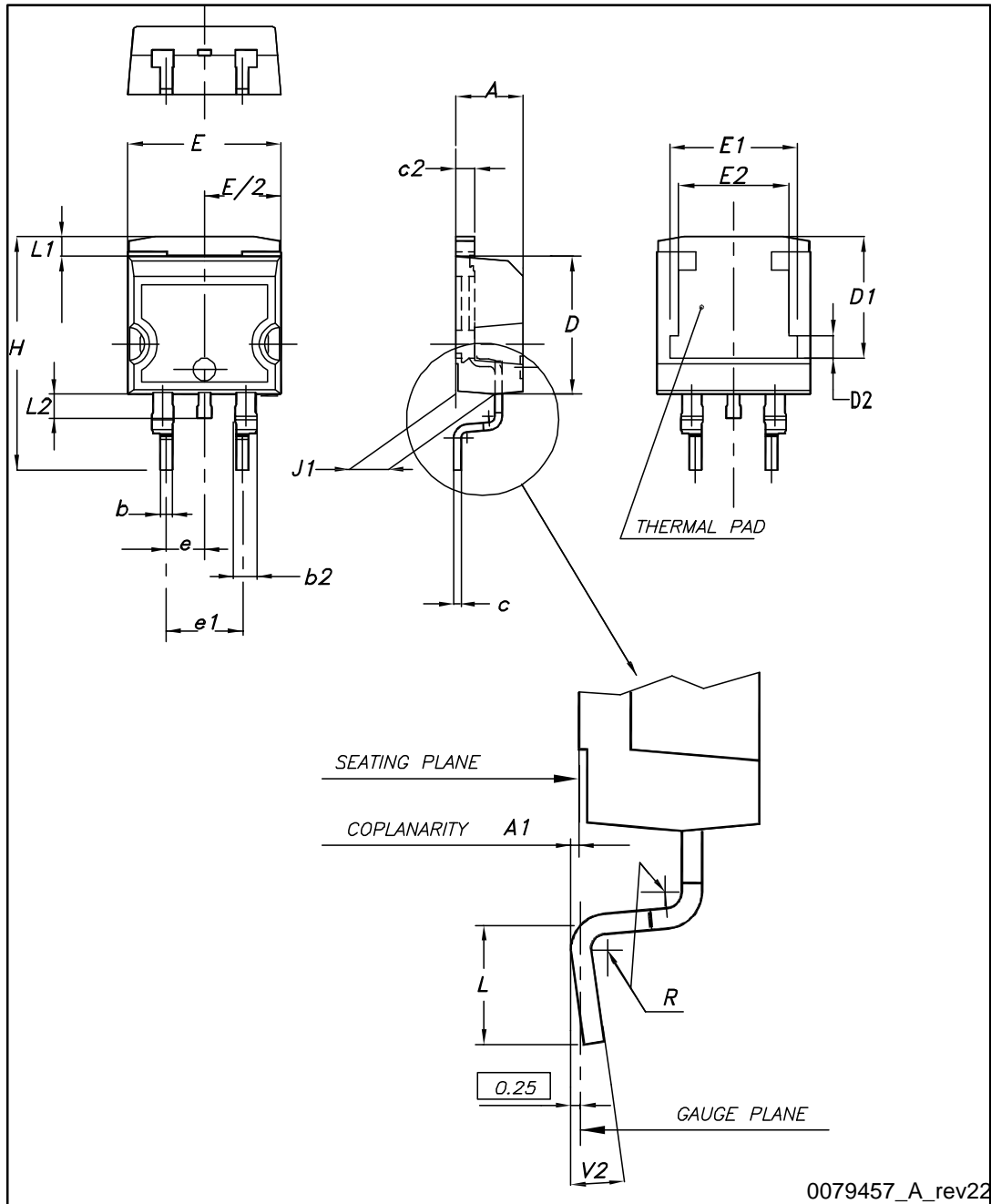
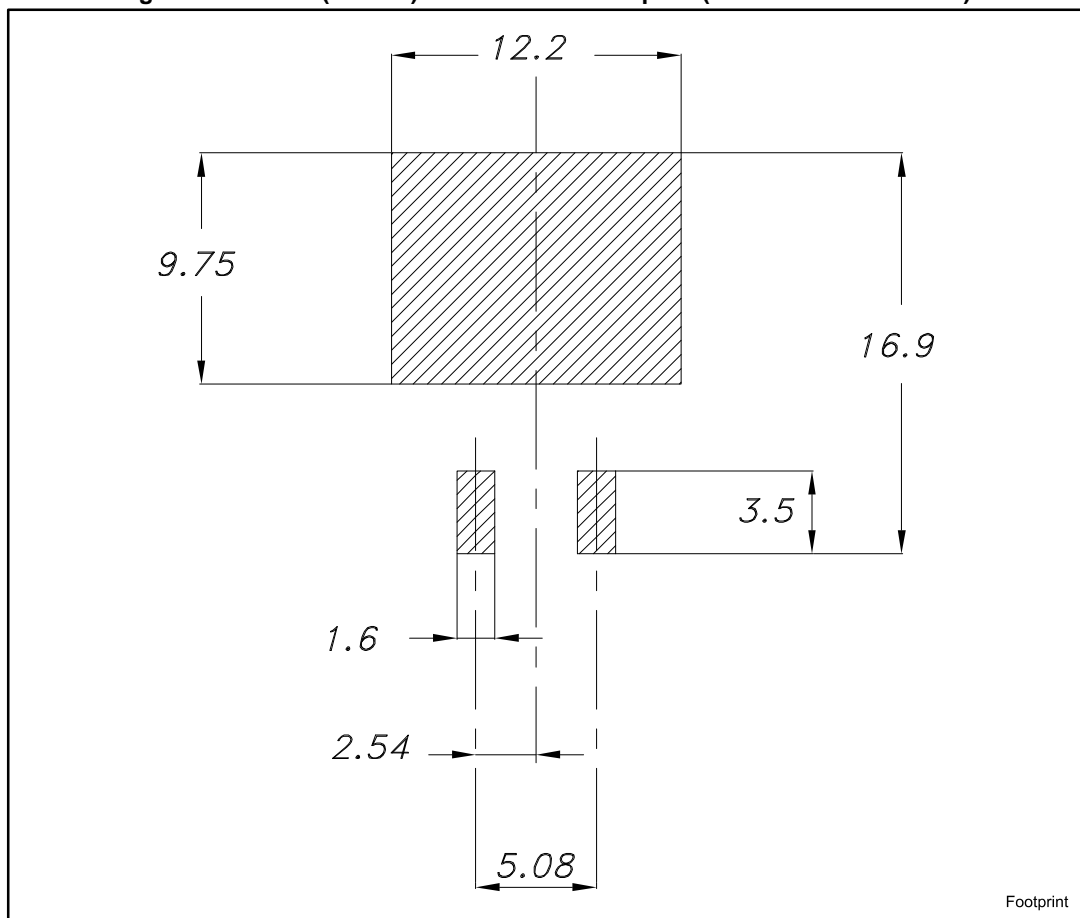


Table 8: D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 20: D²PAK (TO-263) recommended footprint (dimensions are in mm)



4.2 D²PAK packing information

Figure 21: Tape outline

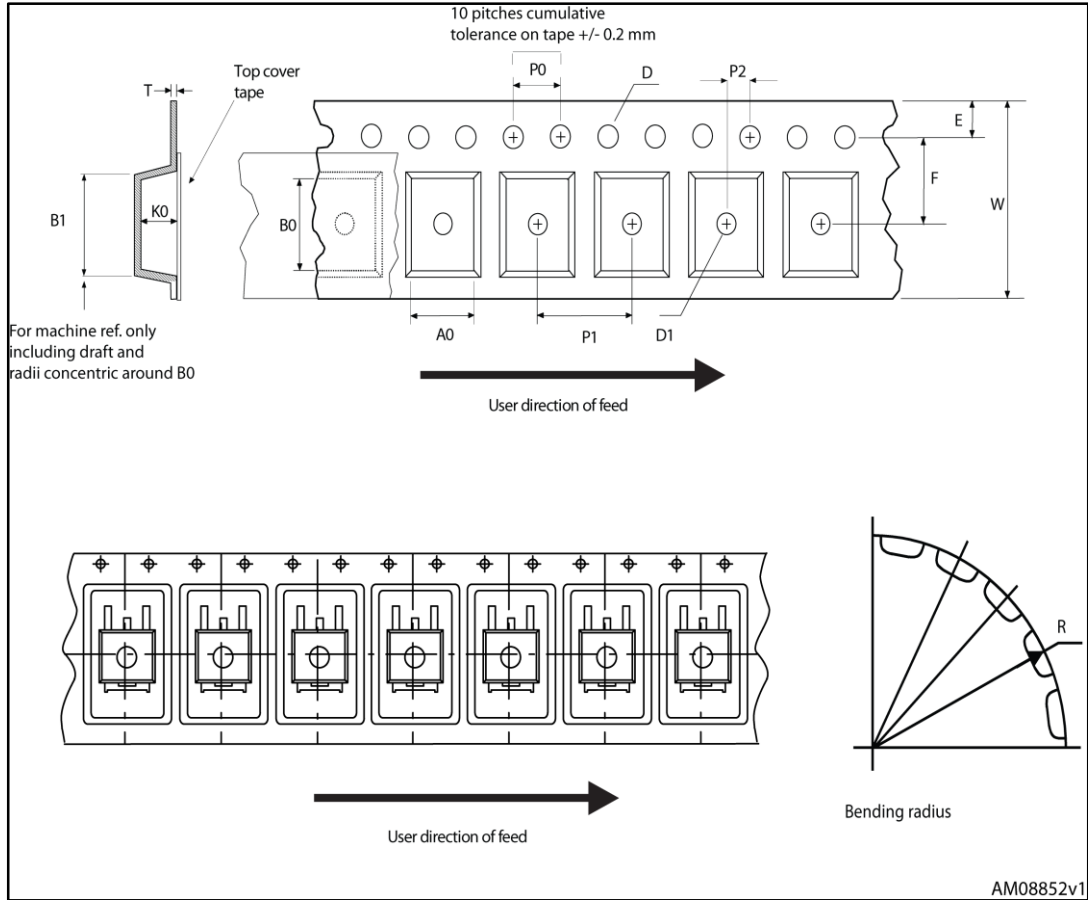


Figure 22: Reel outline

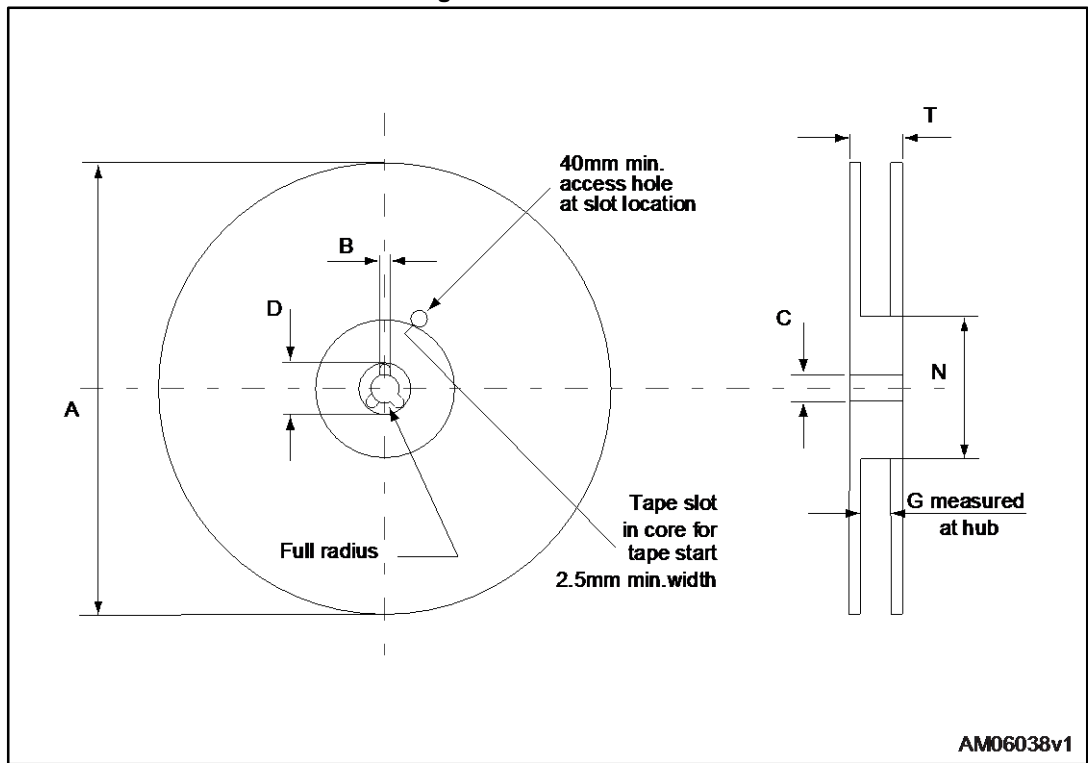


Table 9: D²PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
16-Jun-2015	1	Initial release
18-Nov-2015	2	Document status promoted from preliminary to production data. Updated title and features in cover page.

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